



#### 40V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(on)</sub>            | I <sub>D</sub><br>T <sub>A</sub> = +25°C |
|----------------------|--------------------------------|--|
| -40V                 | 45mΩ @ V <sub>GS</sub> = -10V  | -6.5A                                    |
|                      | 55mΩ @ V <sub>GS</sub> = -4.5V | -5.9A                                    |

### **Description**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

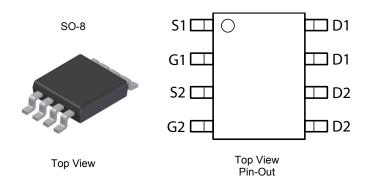
- Backlighting
- DC-DC Converters
- Power Management Functions

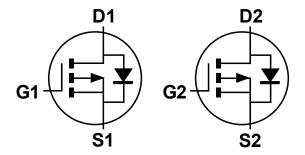
### **Features**

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Totally Lead-Free & Fully RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208<sub>(€3)</sub>
- Weight: 0.074 grams (approximate)





**Equivalent Circuit** 

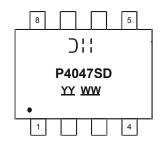
### Ordering Information (Note 4 & 5)

| Part Number    | Compliance | Case | Packaging         |
|----------------|------------|------|-------------------|
| DMP4047SSD-13  | Standard   | SO-8 | 2,500/Tape & Reel |
| DMP4047SSDQ-13 | Automotive | SO-8 | 2,500/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



☐ Manufacturer's Marking
☐ P4047SD = Product Type Marking Code
☐ YYWW = Date Code Marking
☐ YY = Year (ex: 09 = 2009)
☐ WW = Week (01 - 53)



## **Maximum Ratings** (@ $T_A$ = +25°C, unless otherwise specified.)

| Characteristic  |                 |  | Symbol           | Value        | Units |
|---|-----------------|--|------------------|--------------|-------|
| Drain-Source Voltage  |                 |  | $V_{DSS}$        | -40          | V     |
| Gate-Source Voltage   |                 |  | V <sub>GSS</sub> | ±20          | V     |
| Continuous Drain Current (Note 7) V = 40V   | Steady<br>State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | l <sub>D</sub>   | -5.1<br>-4.1 | А     |
| Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V t < 10s  |                 | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | -6.5<br>-5.2 | А     |
| $\begin{array}{ccc} & & & & \\ Steady & & T_A = +25^{\circ}C \\ State & & T_A = +70^{\circ}C \end{array}$ |                 | I <sub>D</sub>                                   | -4.6<br>-3.7     | А            |       |
| Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V   | t < 10s         | $T_A = +25^{\circ}C$<br>$T_A = +70^{\circ}C$     | I <sub>D</sub>   | -5.9<br>-4.7 | А     |
| Maximum Body Diode Continuous Current   |                 |  | Is               | -2.5         | Α     |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%)  |                 |  | I <sub>DM</sub>  | -40          | А     |

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   |                        | Symbol                           | Value       | Units |  |
|--|------------------------|----------------------------------|-------------|-------|--|
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | D                                | 1.3         | 10/   |  |
|  | T <sub>A</sub> = +70°C | $P_{D}$                          | 0.8         | W     |  |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state           | D                                | 98          | °C/W  |  |
|  | t < 10s                | $R_{\theta JA}$                  | 59          |       |  |
| Total Davier Dissipation (Note 7)                | T <sub>A</sub> = +25°C | П                                | 1.8         | W     |  |
| Total Power Dissipation (Note 7)                 | T <sub>A</sub> = +70°C | $P_{D}$                          | 1.1         |       |  |
| Thermal Decistance Junction to Ambient (Note 7)  | Steady state           | D                                | 71          | °C/W  |  |
| Thermal Resistance, Junction to Ambient (Note 7) | t < 10s                | $R_{\theta JA}$                  | 43          |       |  |
| Thermal Resistance, Junction to Case (Note 7)    |                        | $R_{\theta JC}$                  | 11.8        |       |  |
| Operating and Storage Temperature Range          |                        | T <sub>J,</sub> T <sub>STG</sub> | -55 to +150 | °C    |  |

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol               | Min  | Тур   | Max  | Unit | Test Condition   |  |
|--|----------------------|------|-------|------|------|--|--|
| OFF CHARACTERISTICS (Note 8)                           |                      | I .  |       |      |      |  |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>    | -40  | _     | -    | V    | $V_{GS} = 0V, I_D = -250\mu A$                               |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>     | _    | _     | -1   | μA   | V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V                 |  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>     | -    | -     | ±100 | nA   | $V_{GS} = \pm 20V, V_{DS} = 0V$                              |  |
| ON CHARACTERISTICS (Note 8)                            |                      |      |       |      |      |  |  |
| Gate Threshold Voltage                                 | V <sub>GS(th)</sub>  | -1.0 | _     | -3.0 | V    | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                        |  |
| Statia Drain Source On Begintenes                      |                      |      | 33    | 45   |      | $V_{GS} = -10V, I_D = -4.4A$                                 |  |
| Static Drain-Source On-Resistance                      | R <sub>DS</sub> (ON) | _    | 40    | 55   | mΩ   | $V_{GS} = -4.5V$ , $I_D = -3.7A$                             |  |
| Diode Forward Voltage                                  | V <sub>SD</sub>      | -    | -0.75 | -1.2 | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.9A                 |  |
| DYNAMIC CHARACTERISTICS (Note 9)                       |                      |      | •     |      |      | •  |  |
| Input Capacitance                                      | Ciss                 | _    | 1154  | -    | pF   | .,   |  |
| Output Capacitance                                     | Coss                 | -    | 84    | -    | pF   | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V,<br>-f = 1.0MHz |  |
| Reverse Transfer Capacitance                           | Crss                 | -    | 66    | -    | pF   | T = 1.0MHZ   |  |
| Gate Resistance  | RG                   | -    | 12.6  | -    | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                   |  |
| Total Gate Charge (V <sub>GS</sub> = -4.5V)            | Qg                   | _    | 10.6  | -    | nC   |  |  |
| Total Gate Charge (V <sub>GS</sub> = -10V)             | Qg                   | _    | 21.5  | -    | nC   | \/ = 20\/ I= = 4.0A  |  |
| Gate-Source Charge                                     | Qgs                  | -    | 2.2   | -    | nC   | $V_{DS} = -20V, I_D = -4.9A$                                 |  |
| Gate-Drain Charge                                      | Qgd                  | _    | 3.3   | _    | nC   | 1  |  |
| Turn-On Delay Time                                     | tD(on)               | _    | 8.7   | _    | ns   |  |  |
| Turn-On Rise Time                                      | tr                   | -    | 19.6  | -    | ns   | $V_{DS} = -20V, I_{D} = -3.9A$                               |  |
| Turn-Off Delay Time                                    | tD(off)              | 1    | 34.9  | -    | ns   | $V_{GS} = 4.5V, R_{G} = 1\Omega$                             |  |
| Turn-Off Fall Time                                     | tf                   | 1    | 25.5  | -    | ns   | <u>]                                    </u>                 |  |
| Body Diode Reverse Recovery Time                       | trr                  | -    | 9.61  | _    | ns   | I_ = 2.04 di/dt = 1004/ug                                    |  |
| Body Diode Reverse Recovery Charge                     | Qrr                  | _    | 3.3   | _    | nC   | $I_F = -3.9A$ , di/dt = 100A/ $\mu$ s                        |  |

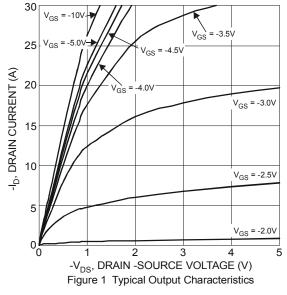
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

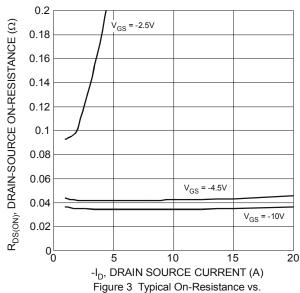
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing. Notes:







Drain Current and Gate Voltage

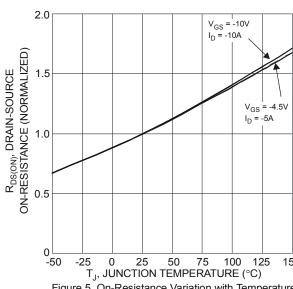


Figure 5 On-Resistance Variation with Temperature

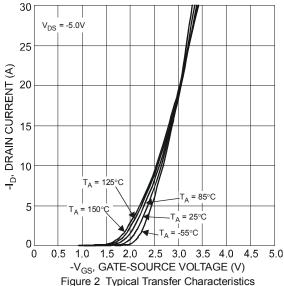
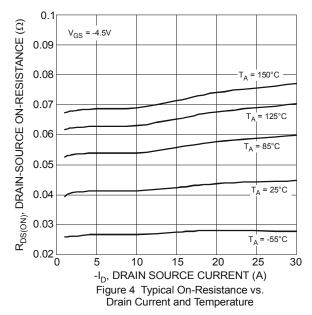


Figure 2 Typical Transfer Characteristics



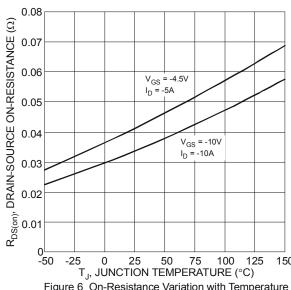


Figure 6 On-Resistance Variation with Temperature



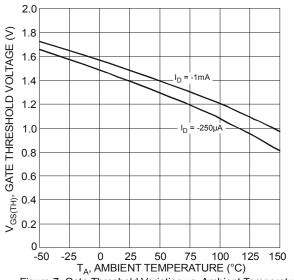


Figure 7 Gate Threshold Variation vs. Ambient Temperature

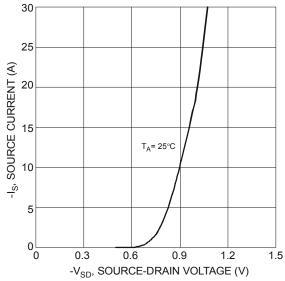
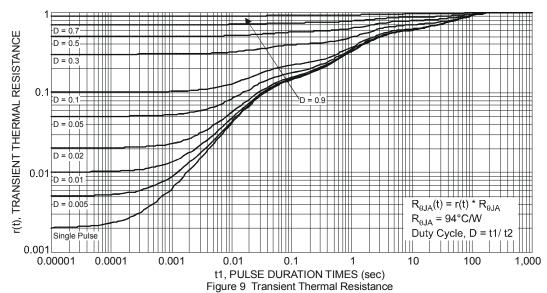
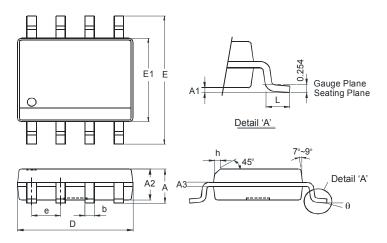


Figure 8 Diode Forward Voltage vs. Current



### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

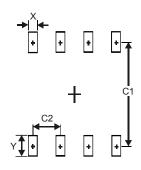


| SO-8                 |                   |      |  |  |
|----------------------|-------------------|------|--|--|
| Dim                  | Min               | Max  |  |  |
| Α                    | -                 | 1.75 |  |  |
| A1                   | 0.10              | 0.20 |  |  |
| A2                   | 1.30              | 1.50 |  |  |
| A3                   | 0.15              | 0.25 |  |  |
| b                    | 0.3               | 0.5  |  |  |
| D                    | 4.85              | 4.95 |  |  |
| Е                    | 5.90              | 6.10 |  |  |
| E1                   | 3.85              | 3.95 |  |  |
| е                    | <b>e</b> 1.27 Typ |      |  |  |
| h                    | -                 | 0.35 |  |  |
| L                    | 0.62              | 0.82 |  |  |
| θ                    | 0°                | 8°   |  |  |
| All Dimensions in mm |                   |      |  |  |



## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Х          | 0.60          |
| Υ          | 1.55          |
| C1         | 5.4           |
| C2         | 1.27          |

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